

PNP TRANSISTOR**8550****-1.5A**

TO-92

- Power Dissipation: 1.0W
- Collector Current: -1.5A
- Collector-Base Voltage: -45V

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (Ta=25)

| PARAMETERS | SYMBOL | MIN | TYP | MAX | UNIT | CONDITION |
|--------------------------------------|--------------------------------------|----------|-----|------|----------|---|
| Collector-Emitter Breakdown Voltage | BV _{ceo} | -25 | | | V | I _c =-0.1mA |
| Collector-Base Breakdown Voltage | BV _{cbo} | -45 | | | V | I _c =-100μA |
| Emitter-Base Breakdown Voltage | BV _{ebo} | -5 | | | V | I _e =-100 μ A |
| Collector-Base Leakage | I _{cbo} | | | -0.1 | μA | V _{cb} =-40V |
| Collector-Emitter Leakage | I _{ceo} | | | -0.1 | μA | V _{ce} =-20V |
| Emitter-Base Leakage | I _{ebo} | | | -0.1 | μA | V _{eb} =-5V |
| Collector-Emitter Saturation Voltage | V _{ce(sat)} | | | -0.6 | V | I _c =-1500mA, I _b =-50mA |
| Base-Emitter Saturation Voltage | V _{be(sat)} | | | -1.2 | V | I _c =-1500mA, I _b =-50mA |
| DC Current Gain | H _{fe1} H _{fe2} | 85 50 | | 300 | | V _{ce} =-1V, I _c =-50mA V _{ce} =-1V, I _c =-500mA |
| Collector Current | I _c | | | -0.5 | A | |
| Peak Collector Current | I _{cp} | | | -8 | A(Pulse) | |
| Current Gain Bandwidth | f _r | 150 | | | MHz | V _{cb} =-6V, I _c =-20mA |
| Output Capacitance | C _{ob} | | | 32 | pF | V _{cb} =-20V, I _e =0, f=1MHz |
| Power Dissipation | P _c | | | 1.0 | W | |
| Junction Temperature | T _j | | | 150 | | |
| Storage Temperature | T _{stg} | -55 | | 150 | | |

Hfe1 Classification

| Rank | B | C | D |
|-------|--------|---------|---------|
| Range | 85-160 | 120-200 | 160-300 |

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